High Power Laser Diode Bar

Part Number: BAR-105

High Power 19 Emitters Bar Multi-Mode Fabry-Perot CW Wavelength at 1470nm

Features

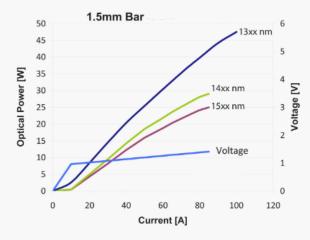
- High Output Power
- High Dynamic Range
- High Efficiency
- Standard 19 Emitters Bar
- Cost Effective

Application

- Professional Medical
- Home Medical
- Laser Rangefinder

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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BAR-105

Optical	Symbol	Тур.	Units
Center Wavelength	λ _c	1470	nm (±20)
Output Power (CW)*	Pout	20	watts (±10%)
Chip Cavity Length	CL	1500	μm
Emitter Width	W	95	μm
Number of Emitters		19	
Spectral Width FWHM	Δλ	15	nm
Slope Efficiency	η	0.4	W/A
Fast Axis Div.	Θ⊥	25	deg FWHM
Slow Axis Div.	Θ _{II}	8	deg FWHM
			5
Electrical	Symbol		Units
Electrical Power Conversion Eff.	i iii	30	
	Symbol	30 10	Units
Power Conversion Eff.	Symbol η		Units %
Power Conversion Eff. Threshold Current	Symbol η ΙτΗ	10	Units % A
Power Conversion Eff. Threshold Current Operating Current	Symbol ŋ Ітн Іор	10 60	Units % A A
Power Conversion Eff. Threshold Current Operating Current Operating Voltage	Symbol ŋ Ітн Іор	10 60 1.3	Units % A A V

*Specified values are rated at a constant heat sink temperature of 20°C.

**High temperature operation will reduce performance and MTTF.

Unless otherwise indicated all values are nominal.

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Mechanical Drawing



BAR ATTRIBUTES

APERTURE WIDTH (µm)	Multi Mode (95) ± 3
BAR WIDTH (mm)	10 ± 0.01
THICKNESS (µm)	160 ± 10
CAVITY LENGTH (µm)	Varies ± 10

P METALIZATION

MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	50	± 10
Pt	125	± 25
Au	250	± 50

Pt	125	± 25
Au	250	± 50

MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	30	± 10
Pt	125	± 25
Au	400	± 40

N METALIZATION

10.00 - 19 EMITTERS 500µm PITCH CAVITY LENGTH TRIANGLE ON P-SIDE POINTS TOWARDS FRONT FACET PATTERNED P-SIDE FULLY METALIZED SURFACE 0.16 N-SIDE FULLY METALIZED SURFACE

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